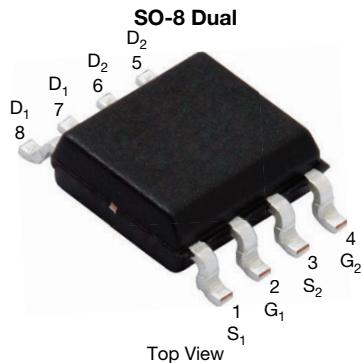


## Dual N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
$V_{DS}$ (V)	60
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 10$ V	0.040
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 4.5$ V	0.055
$I_D$ (A) per leg	7
Configuration	Dual

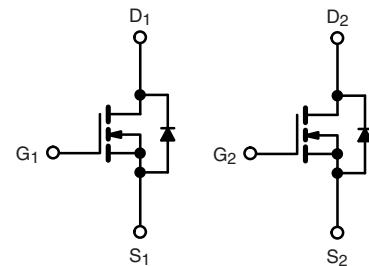


### FEATURES

- TrenchFET® power MOSFET
- 100 %  $R_g$  and UIS tested



**RoHS**  
COMPLIANT  
**HALOGEN**  
**FREE**



ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current	$I_D$	7	A
$T_C = 125$ °C		4	
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	3.6	
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	28	
Single Pulse Avalanche Current	$I_{AS}$	18	
Single Pulse Avalanche Energy	$E_{AS}$	16.2	mJ
Maximum Power Dissipation <sup>b</sup>	$P_D$	4	W
$T_C = 125$ °C		1.3	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +175	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	$R_{thJA}$	110	°C/W
Junction-to-Foot (Drain)	$R_{thJF}$	34	

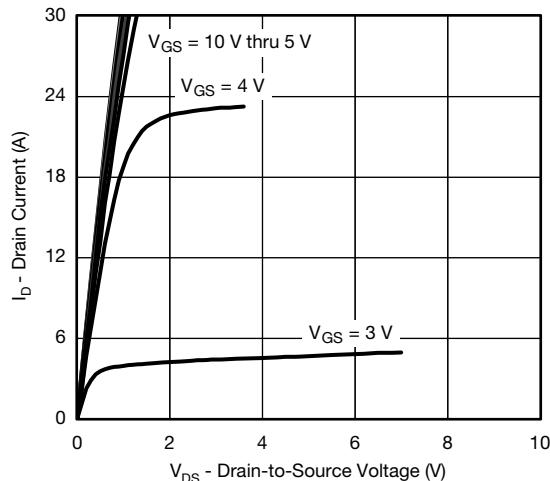
### Notes

- Package limited.
- Pulse test; pulse width  $\leq 300$   $\mu$ s, duty cycle  $\leq 2$  %.
- When mounted on 1" square PCB (FR4 material).

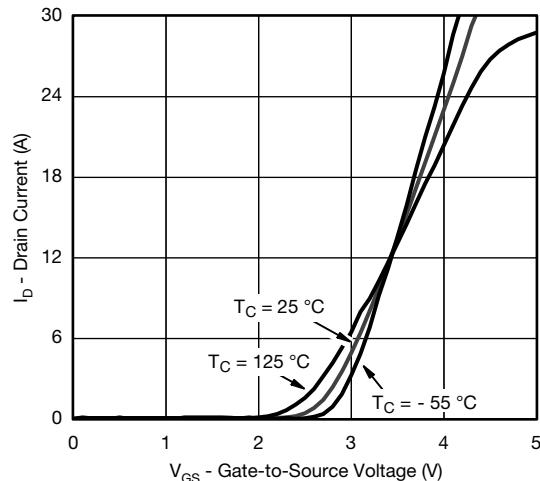
SPECIFICATIONS ( $T_C = 25^\circ\text{C}$ , unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
<b>Static</b>								
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$		60	-	-	V	
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$		1.5	2.0	2.5		
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}$	-	-	1	$\mu\text{A}$	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}$ , $T_J = 125^\circ\text{C}$	-	-	50		
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}$ , $T_J = 175^\circ\text{C}$	-	-	150		
On-State Drain Current <sup>a</sup>	$I_{D(\text{on})}$	$V_{GS} = 10\text{ V}$	$V_{DS} \geq 5\text{ V}$	20	-	-	A	
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(\text{on})}$	$V_{GS} = 10\text{ V}$	$I_D = 4.5\text{ A}$ -		0.028	0.040	$\Omega$	
		$V_{GS} = 10\text{ V}$	$I_D = 4.5\text{ A}$ , $T_J = 125^\circ\text{C}$	-	-	0.066		
		$V_{GS} = 10\text{ V}$	$I_D = 4.5\text{ A}$ , $T_J = 175^\circ\text{C}$	-	-	0.081		
		$V_{GS} = 4.5\text{ V}$	$I_D = 4\text{ A}$ -		0.030	0.055		
Forward Transconductance <sup>f</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}$ , $I_D = 4.5\text{ A}$		-	15	-	S	
<b>Dynamic <sup>b</sup></b>								
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$	-	600	750	pF	
Output Capacitance	$C_{oss}$			-	110	140		
Reverse Transfer Capacitance	$C_{rss}$			-	50	62		
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}$ , $I_D = 5.3\text{ A}$	-	11.7	18	nC	
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			-	1.8	2.7		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			-	2.8	4.2		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		1.3	-	6	$\Omega$	
Turn-On Delay Time <sup>c</sup>	$t_{d(\text{on})}$	$V_{DD} = 30\text{ V}$ , $R_L = 6.8\text{ }\Omega$ $I_D \approx 4.4\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 1\text{ }\Omega$		-	7	11	ns	
Rise Time <sup>c</sup>	$t_r$			-	3.3	5		
Turn-Off Delay Time <sup>c</sup>	$t_{d(\text{off})}$			-	22.4	33.5		
Fall Time <sup>c</sup>	$t_f$			-	2.1	3.2		
<b>Source-Drain Diode Ratings and Characteristics <sup>b</sup></b>								
Pulsed Current <sup>a</sup>	$I_{SM}$			-	-	28	A	
Forward Voltage	$V_{SD}$	$I_F = 2\text{ A}$ , $V_{GS} = 0\text{ V}$		-	0.75	1.1	V	

**Notes**

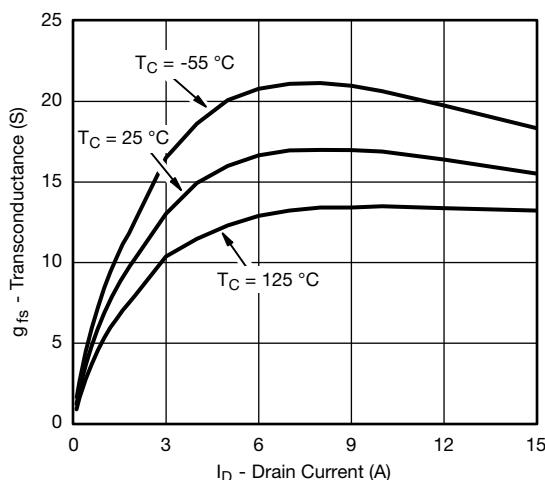
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\text{ \%}$ .
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

**TYPICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)


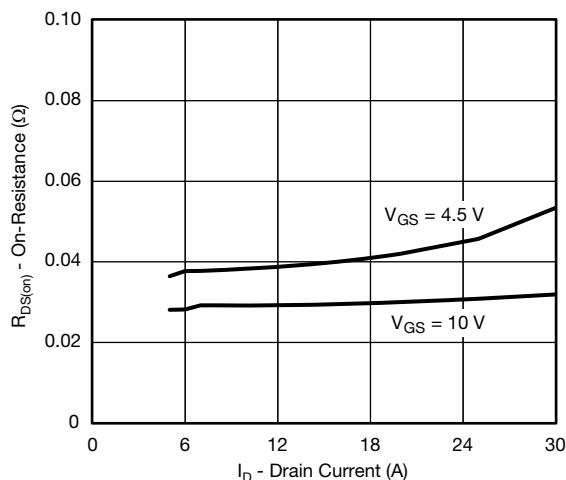
Output Characteristics



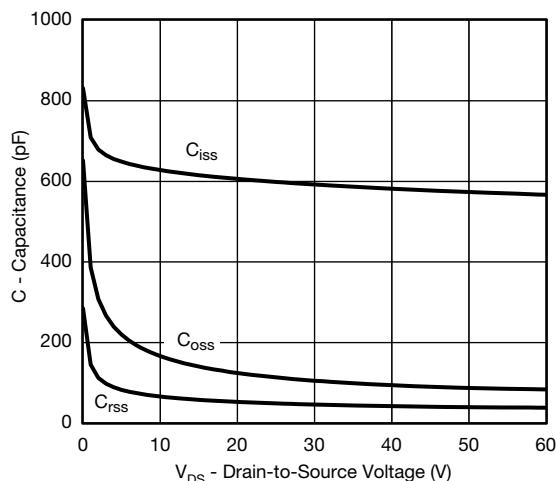
Transfer Characteristics



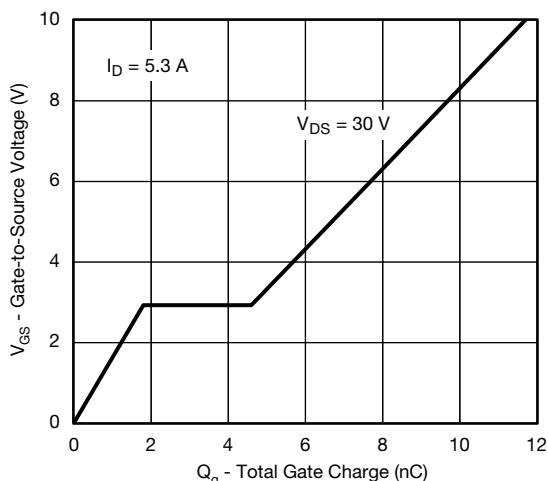
Transconductance



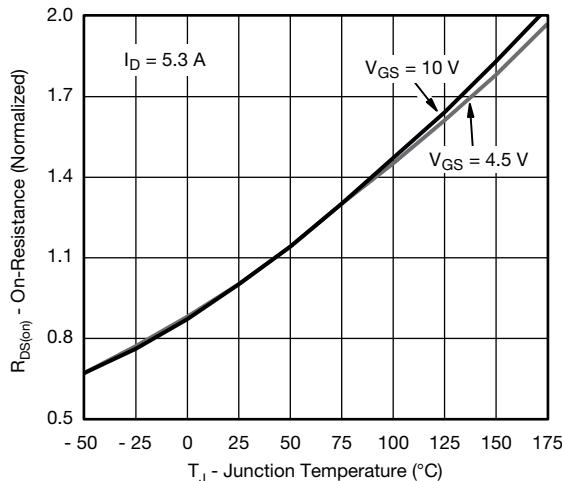
On-Resistance vs. Drain Current



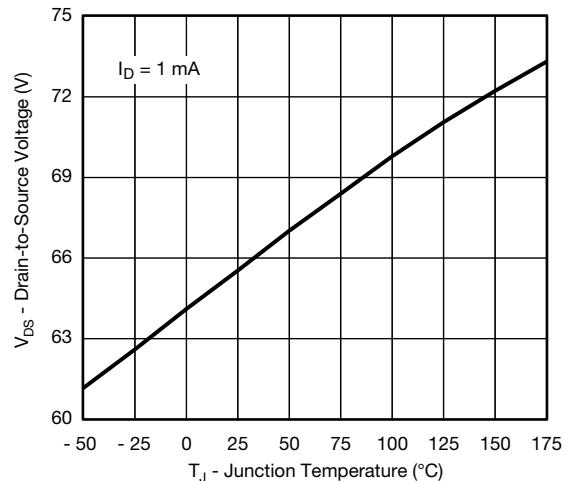
Capacitance



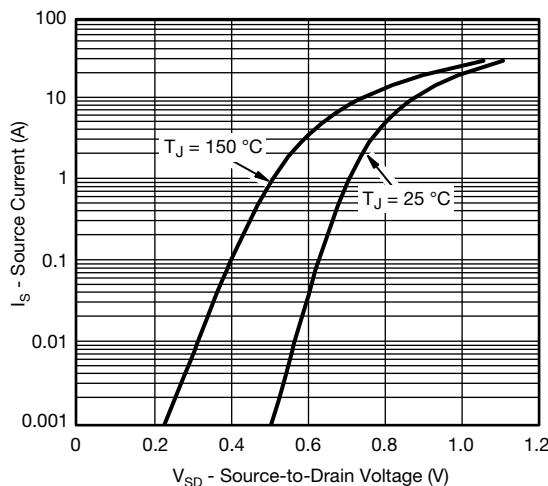
Gate Charge

**TYPICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)


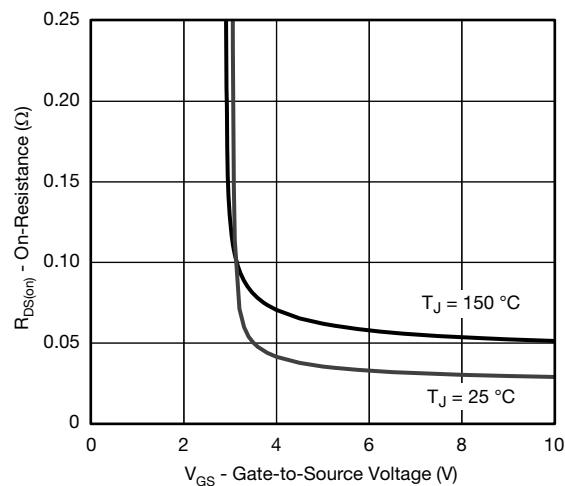
On-Resistance vs. Junction Temperature



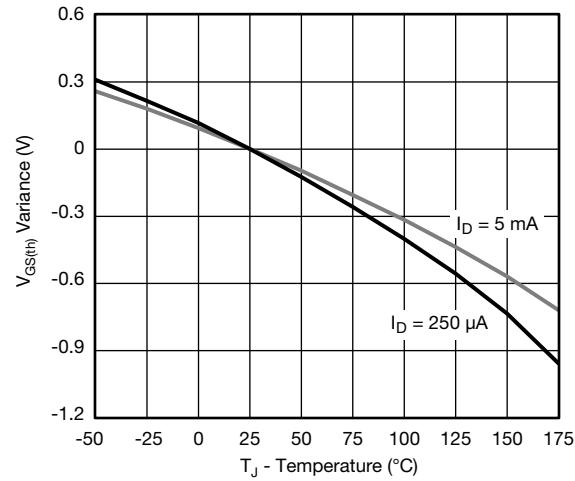
Drain Source Breakdown vs. Junction Temperature



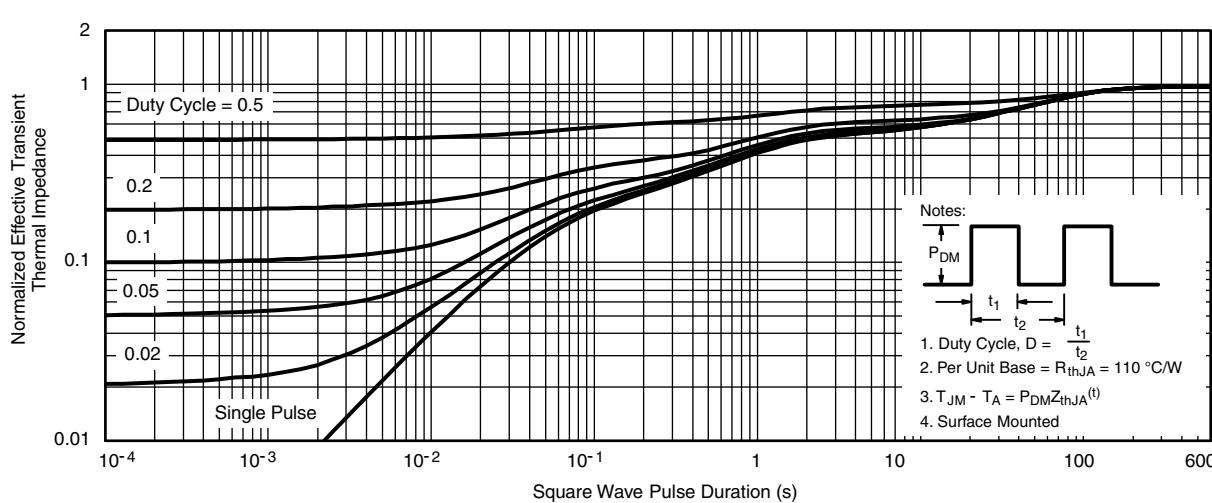
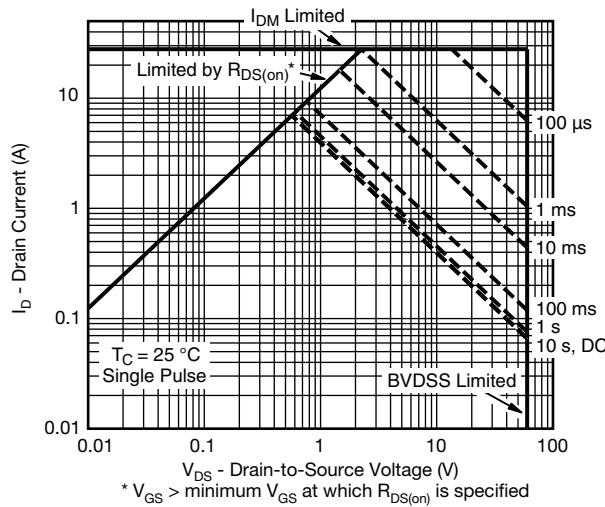
Source Drain Diode Forward Voltage

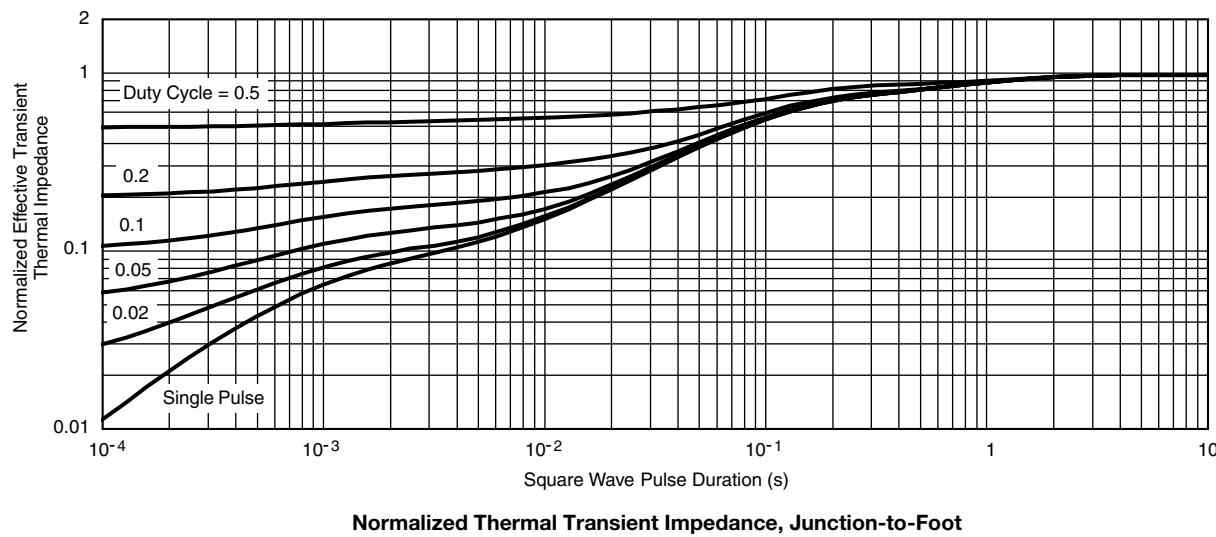


On-Resistance vs. Gate-to-Source Voltage



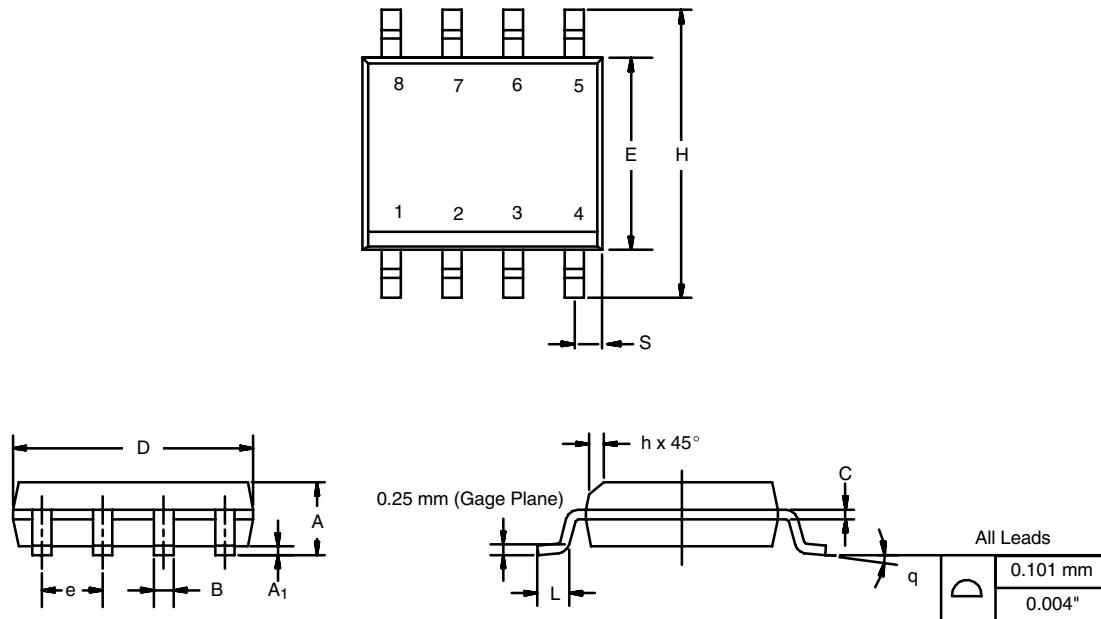
Threshold Voltage

**THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)**


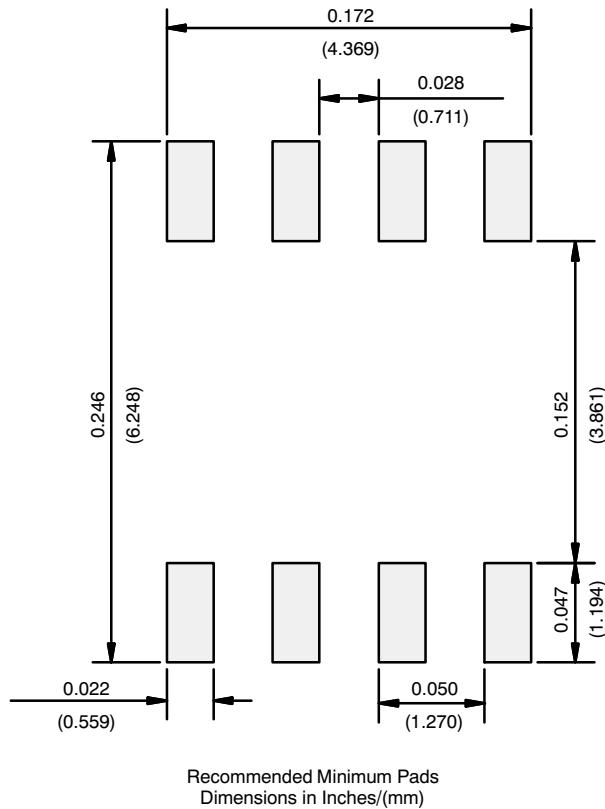
**THERMAL RATINGS** ( $T_A = 25$  °C, unless otherwise noted)

## SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

**RECOMMENDED MINIMUM PADS FOR SO-8**

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